



JR0205 Series Sensitive gate SCRs

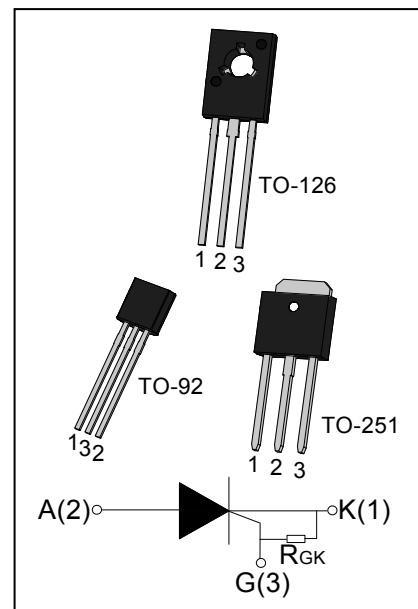
Rev.9.0

DESCRIPTION:

The JR0205 SCR series with the parallel resistor between Gate and Cathode are especially recommended for use on straight hair, igniter, anion generator, etc. All the packages mentioned are RoHS compliant. (2011/65/EU)

MAIN FEATURES

| Symbol | Value | Unit |
|--------------|------------|---------|
| $I_{T(RMS)}$ | 2 | A |
| I_{GT} | ≤ 200 | μA |
| V_{TM} | ≤ 1.5 | V |



ABSOLUTE MAXIMUM RATINGS

| Parameter | Symbol | Value | Unit |
|---|--------------|----------------------|-----------|
| Storage junction temperature range | T_{stg} | -40-150 | °C |
| Operating junction temperature range | T_j | -40-125 ^① | °C |
| Repetitive peak off-state voltage | V_{DRM} | 600 | V |
| Repetitive peak reverse voltage | V_{RRM} | 600 | V |
| RMS on-state current | $I_{T(RMS)}$ | 2 | A |
| TO-92 ($T_c=60^\circ C$) | | | |
| TO-251/ TO-126 ($T_c=72^\circ C$) | | | |
| Non repetitive surge peak on-state current (tp=10ms) | I_{TSM} | 20 | A |
| I^2t value for fusing (tp=10ms) | I^2t | 2 | A^2s |
| Critical rate of rise of on-state current | di/dt | 50 | $A/\mu s$ |
| Peak gate current (tp=20μs, $T_j=125^\circ C$) | I_{GM} | 0.2 | A |
| Peak gate power (tp=20μs, $T_j=125^\circ C$) | P_{GM} | 0.5 | W |
| Average gate power dissipation($T_j=125^\circ C$) | $P_{G(AV)}$ | 0.1 | W |

NOTE 1: When we parallel connect a $\leq 1\text{K}\Omega$ resistor between Gate and Cathode, the T_j can reach $125^\circ C$; if without this resistor, the T_j only can reach $110^\circ C$.

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

| Symbol | Test Condition | Value | | | Unit |
|----------|--|-------|------|------|------------------|
| | | MIN. | TYP. | MAX. | |
| I_{GT} | $V_D=12V$ $R_L=33\Omega$ | - | 40 | 200 | μA |
| V_{GT} | | - | 0.5 | 0.8 | V |
| V_{GD} | $V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ | 0.2 | - | - | V |
| I_L | $I_G=1.2 I_{GT}$ | - | - | 3 | mA |
| I_H | $I_T=0.05A$ | - | - | 2 | mA |
| dV/dt | $V_D=60\%V_{DRM}$ $T_j=125^\circ\text{C}$ $R_{GK}=1\text{K}\Omega$ | 10 | - | - | V/ μs |

STATIC CHARACTERISTICS

| Symbol | Parameter | Value(MAX) | Unit |
|-----------|----------------------------------|------------|---------------|
| V_{TM} | $I_{TM}=4A$ $t_p=380\mu\text{s}$ | 1.5 | V |
| I_{DRM} | $V_D=V_{DRM}$ $V_R=V_{RRM}$ | 5 | μA |
| I_{RRM} | | 100 | μA |

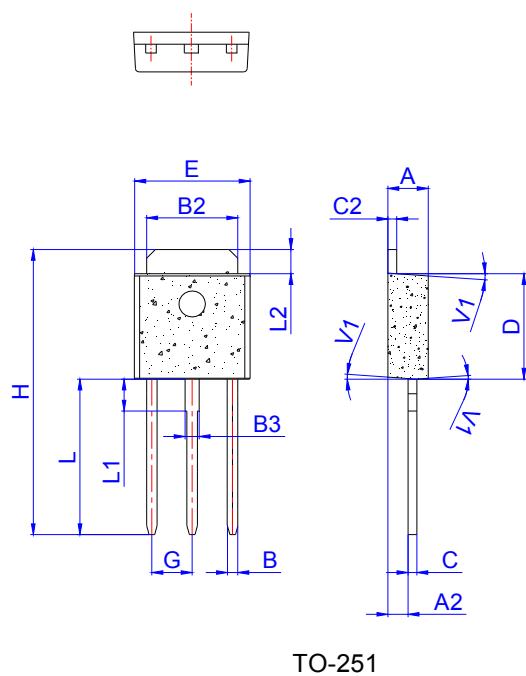
THERMAL RESISTANCES

| Symbol | Parameter | Value | Unit |
|---------------|------------------|-------|---------------------------|
| $R_{th(j-c)}$ | junction to case | 30 | $^\circ\text{C}/\text{W}$ |
| | | 6.5 | |

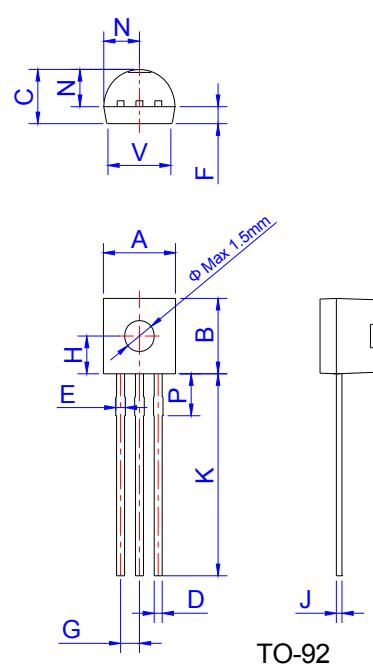
ORDERING INFORMATION

| | | | | | |
|---------------------------------|---|----------------------------------|----|------------|---------------------------------|
| J | R | 02 | 05 | H | U:TO-92 H:TO-251 Q:TO-126 |
| JieJie Microelectronics Co.,Ltd | | 05: $I_{GT} \leq 200\mu\text{A}$ | | IT(RMS):2A | |
| Sensitive gate SCRs | | | | | |

PACKAGE MECHANICAL DATA

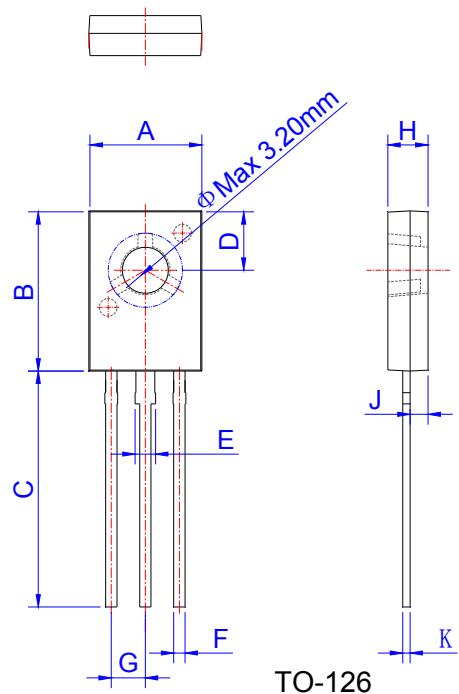


| Ref. | Dimensions | | | | | |
|------|-------------|------|------|--------|-------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A | 2.20 | | 2.40 | 0.086 | | 0.095 |
| A2 | 0.90 | | 1.20 | 0.035 | | 0.047 |
| B | 0.55 | | 0.65 | 0.022 | | 0.026 |
| B2 | 5.10 | | 5.40 | 0.200 | | 0.213 |
| B3 | 0.76 | | 0.85 | 0.030 | | 0.033 |
| C | 0.45 | | 0.62 | 0.018 | | 0.024 |
| C2 | 0.48 | | 0.62 | 0.019 | | 0.024 |
| D | 6.00 | | 6.20 | 0.236 | | 0.244 |
| E | 6.40 | | 6.70 | 0.252 | | 0.264 |
| G | | 2.30 | | | 0.091 | |
| H | 16.0 | | 17.0 | 0.630 | | 0.669 |
| L | 8.90 | | 9.40 | 0.350 | | 0.370 |
| L1 | 1.80 | | 1.90 | 0.071 | | 0.075 |
| L2 | 1.37 | | 1.50 | 0.054 | | 0.059 |
| V1 | | 4° | | | 4° | |

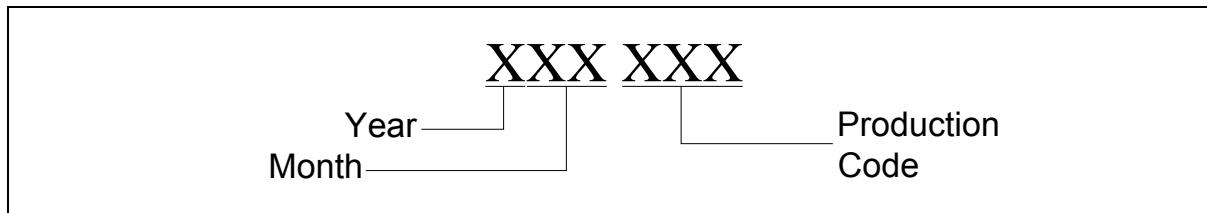
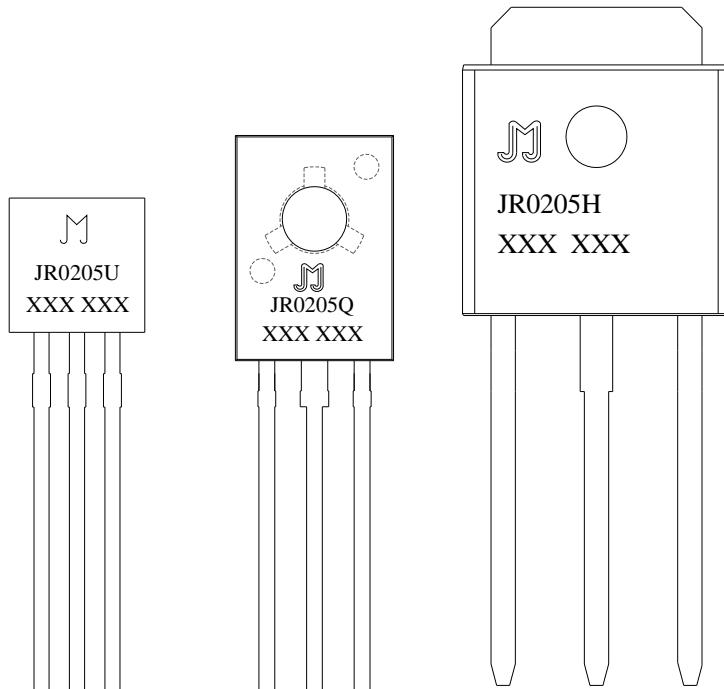


| Ref. | Dimensions | | | | | |
|------|-------------|------|-------|--------|-------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A | 4.45 | | 5.20 | 0.175 | | 0.205 |
| B | 4.32 | | 5.33 | 0.170 | | 0.210 |
| C | 3.18 | | 4.19 | 0.125 | | 0.165 |
| D | 0.407 | | 0.533 | 0.016 | | 0.021 |
| E | 0.50 | | 0.70 | 0.020 | | 0.028 |
| F | - | 1.1 | - | - | 0.043 | - |
| G | - | 1.27 | - | - | 0.050 | - |
| H | - | 2.30 | - | - | 0.091 | - |
| J | 0.36 | | 0.50 | 0.014 | | 0.020 |
| K | 12.70 | | 15.0 | 0.500 | | 0.591 |
| N | 2.04 | | 2.66 | 0.080 | | 0.105 |
| P | 1.86 | | 2.06 | 0.073 | | 0.081 |
| V | - | | 4.3 | - | | 0.169 |

PACKAGE MECHANICAL DATA



| Ref. | Dimensions | | | | | |
|------|-------------|------|------|--------|-------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A | 7.40 | | 7.80 | 0.291 | | 0.307 |
| B | 10.6 | | 11.2 | 0.417 | | 0.441 |
| C | 15.3 | | 16.3 | 0.602 | | 0.642 |
| D | 3.90 | | 4.10 | 0.154 | | 0.161 |
| E | 1.17 | | 1.47 | 0.046 | | 0.058 |
| F | 0.66 | | 0.86 | 0.026 | | 0.034 |
| G | | 2.29 | | | 0.090 | |
| H | 2.50 | | 2.90 | 0.098 | | 0.114 |
| J | 1.10 | | 1.50 | 0.043 | | 0.059 |
| K | 0.45 | | 0.60 | 0.018 | | 0.024 |

MARKING**PACKAGE INFORMATION**

| PACKAGE | OUTLINE | TUBE (PCS) | INNER BOX (PCS) | PER CARTON |
|---------|---------------|---------------|--------------------|------------|
| TO-126 | TUBE | 50 | 3,000 | 18,000 |
| TO-251 | TUBE | 80 | 4,000 | 32,000 |
| PACKAGE | OUTLINE | BAG (PCS) | INNER BOX (PCS) | PER CARTON |
| TO-92 | Shielding Bag | 1,000 | 10,000 | 30,000 |

FIG.1: Maximum power dissipation versus RMS on-state current

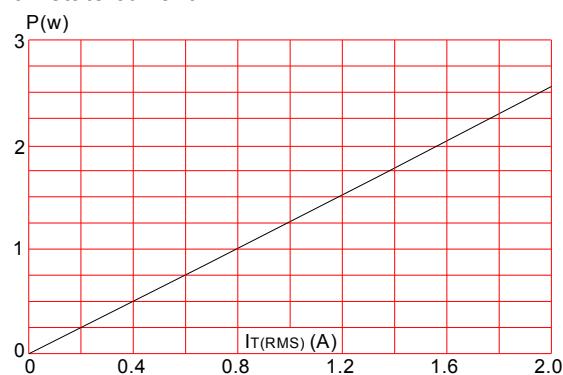


FIG.3: Surge peak on-state current versus number of cycles

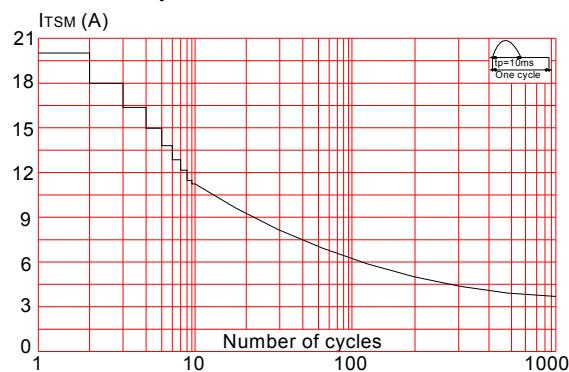


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $tp < 10\text{ms}$, and corresponding value of I^2t ($dI/dt < 50\text{A}/\mu\text{s}$)

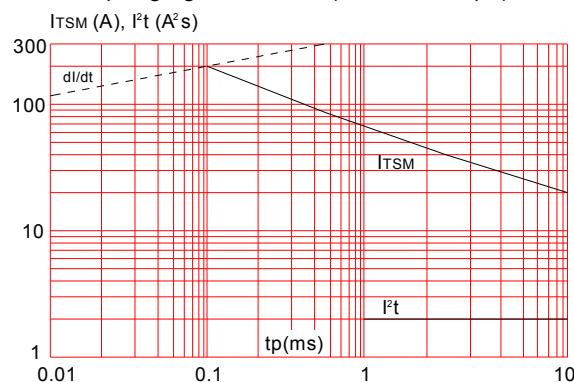


FIG.2: RMS on-state current versus case temperature

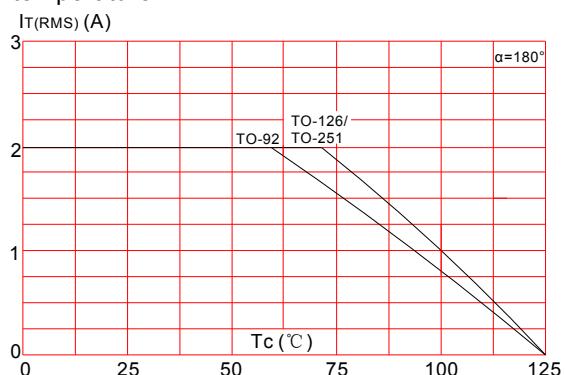


FIG.4: On-state characteristics (maximum values)

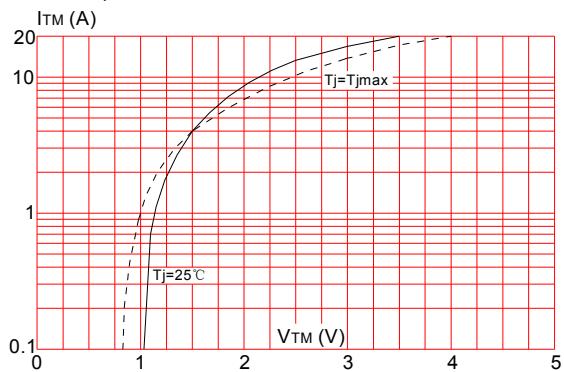
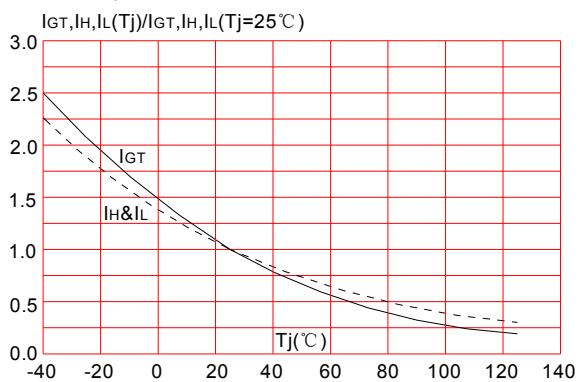


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature





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